



PSMN3R7-30YLC,115 Information



For Reference Only

Part Number PSMN3R7-30YLC,115

Manufacturer NXP

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 100A LFPAK

Package SC-100, SOT-669

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PSMN3R7-30YLC,115 Specifications

Manufacturer Part Number PSMN3R7-30YLC,115 Manufacturer NXP Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SC-100, SOT-669 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1.95V @ 1mA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1848pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SC-100, SOT-669 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1.95V @ 1mA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1848pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-S08 Package / Case SC-100, SOT-669	Manufacturer Part Number	PSMN3R7-30YLC,115
Package SC-100, SOT-669 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1.95V @ 1mA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1848pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Manufacturer	NXP
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Series - Channel FET Type N-Channel Technology MOSFET (Metal Oxide) Jorain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1.95V @ 1mA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1848pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-S08 Package / Case Source (Max) MOSFET (Max) (Mosfer) 100 (Mosfer) 1		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 100A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 199C @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) 30V Rds Qv 4.5V, 10V	Package	SC-100, SOT-669
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **EUV** FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V **EUV** 100A (Tc) 109A (Tc) 119SV @ ImA 119SV @ ImA 119SV @ ImA 119SV @ 10V 119SV @ ImA 119SV @ 10V 119SV @ ImA 129NC @ 10V 129NC @ 10V 1384spF @ 15V 29NC @ 10V 1384spF @ 15	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 30V 100A (Tc) 100A (Tc) 110B (Tc) 110B (Tc) 110B (Te)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1.95V @ 1mA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1848pF @ 15V Vgs (Max) #20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature Fundamental Control of the Control of Surface Mount Supplier Device Package Package / Case 100A (Tc) 10	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1.95V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature Surplier Device Package Package / Case A.5V, 10V 4.5V, 10V 1.95V @ 1mA 1.95V @ 1mO 1.95V @	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1848pF @ 15V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 1.95V @ 1mA 1.95V @ 1nV Input Capacitance (Ciss) (Max) @ Id, Vgs 1.95V @ 15V	Current - Continuous Drain (Id) @ 25°C	100A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jemperature Surface Mount Supplier Device Package Package / Case Package / Case 29nC @ 10V 1848pF @ 15V 1848pF	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 1848pF @ 15V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Vgs(th) (Max) @ Id	1.95V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs3.95 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	Gate Charge (Qg) (Max) @ Vgs	29nC @ 10V
FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Input Capacitance (Ciss) (Max) @ Vds	1848pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.95 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.95 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Power Dissipation (Max)	79W (Tc)
Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Rds On (Max) @ Id, Vgs	3.95 mOhm @ 20A, 10V
Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case SC-100, SOT-669	Mounting Type	Surface Mount
	Supplier Device Package	LFPAK56, Power-SO8
Report errors?	Package / Case	SC-100, SOT-669
		Report errors?

PSMN3R7-30YLC,115 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PSMN3R7-30YLC,115 Payment Methods



















PSMN3R7-30YLC,115 Shipping Methods













If you have any question about PSMN3R7-30YLC,115, please do not hesitate to contact us!

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